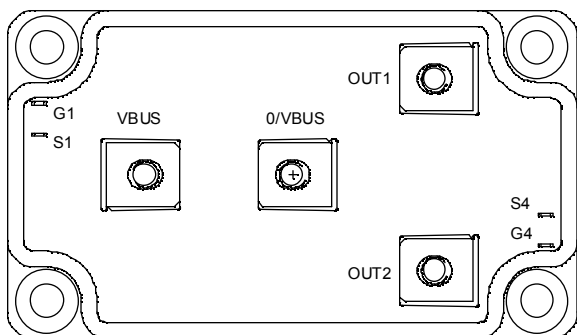
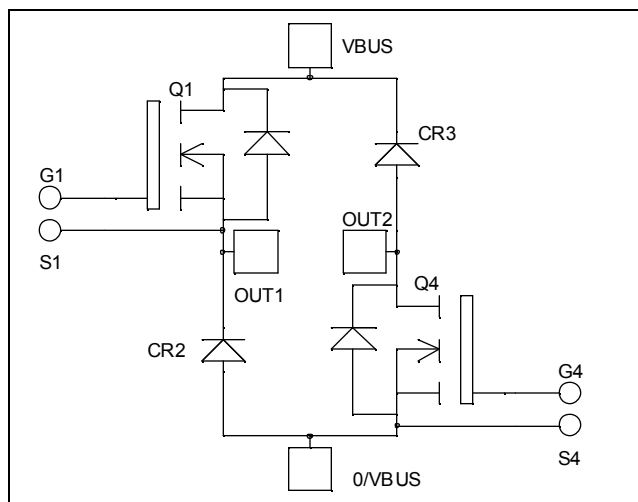


Asymmetrical - bridge MOSFET Power Module

$V_{DSS} = 200V$

$R_{DSon} = 8m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 208A$ @ $T_c = 25^\circ C$



Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	832	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	10	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	100	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 200\text{V}$	$T_j = 25^\circ\text{C}$			375	μA
		$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 160\text{V}$	$T_j = 125^\circ\text{C}$			1500	
$R_{\text{DS(on)}}$	Drain – Source on Resistance	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 104\text{A}$			8	10	$\text{m}\Omega$
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}} = V_{\text{DS}}, I_{\text{D}} = 5\text{mA}$		3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{\text{GS}} = \pm 30\text{V}, V_{\text{DS}} = 0\text{V}$				± 150	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{iss}	Input Capacitance	$V_{\text{GS}} = 0\text{V}$ $V_{\text{DS}} = 25\text{V}$ $f = 1\text{MHz}$		14.4		nF
C_{oss}	Output Capacitance			4.66		
C_{rss}	Reverse Transfer Capacitance			0.29		
Q_{g}	Total gate Charge	$V_{\text{GS}} = 10\text{V}$ $V_{\text{Bus}} = 100\text{V}$ $I_{\text{D}} = 208\text{A}$		280		nC
Q_{gs}	Gate – Source Charge			106		
Q_{gd}	Gate – Drain Charge			134		
$T_{\text{d(on)}}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{\text{GS}} = 15\text{V}$ $V_{\text{Bus}} = 133\text{V}$ $I_{\text{D}} = 208\text{A}$ $R_{\text{G}} = 2.5\Omega$		32		ns
T_{r}	Rise Time			64		
$T_{\text{d(off)}}$	Turn-off Delay Time			88		
T_{f}	Fall Time			116		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{\text{GS}} = 15\text{V}, V_{\text{Bus}} = 133\text{V}$ $I_{\text{D}} = 208\text{A}, R_{\text{G}} = 2.5\Omega$		1698		μJ
E_{off}	Turn-off Switching Energy			1858		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{\text{GS}} = 15\text{V}, V_{\text{Bus}} = 133\text{V}$ $I_{\text{D}} = 208\text{A}, R_{\text{G}} = 2.5\Omega$		1872		μJ
E_{off}	Turn-off Switching Energy			1972		

Diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I_{RM}	Maximum Reverse Leakage Current	$V_{\text{R}} = 200\text{V}$	$T_j = 25^\circ\text{C}$			250	μA
			$T_j = 125^\circ\text{C}$			600	
I_{F}	DC Forward Current		$T_c = 75^\circ\text{C}$		200		A
V_{F}	Diode Forward Voltage	$I_{\text{F}} = 200\text{A}$			1	1.1	V
		$I_{\text{F}} = 400\text{A}$			1.4		
		$I_{\text{F}} = 200\text{A}$	$T_j = 125^\circ\text{C}$		0.9		
t_{rr}	Reverse Recovery Time	$I_{\text{F}} = 200\text{A}$ $V_{\text{R}} = 133\text{V}$ $di/dt = 400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		60		ns
			$T_j = 125^\circ\text{C}$		110		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		400		nC
			$T_j = 125^\circ\text{C}$		1680		

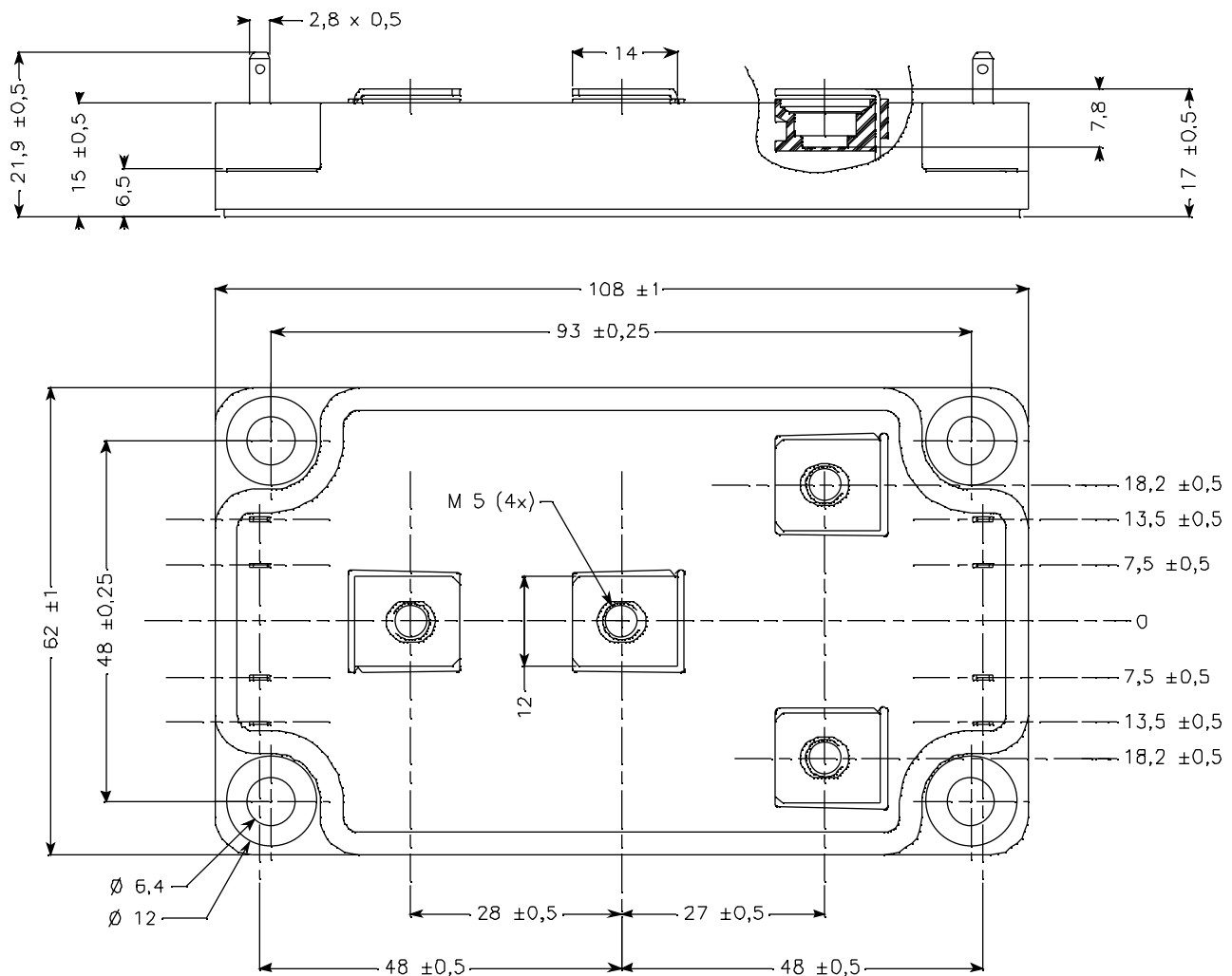
Thermal and package characteristics

Symbol Characteristic

Min Typ Max Unit

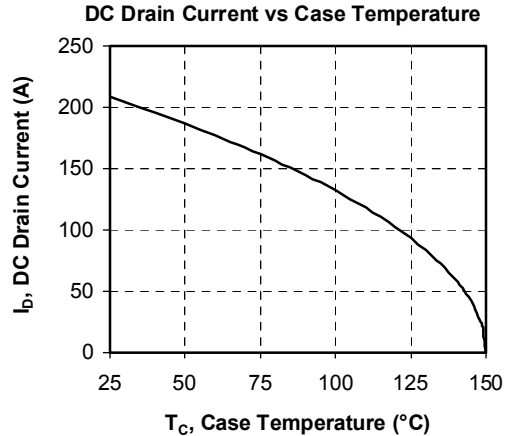
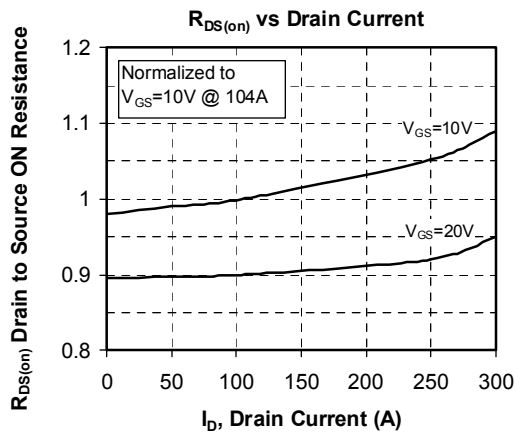
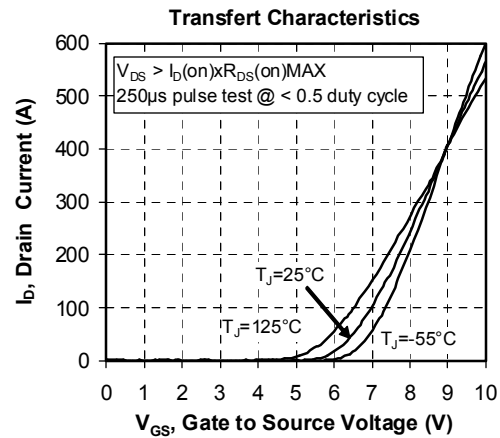
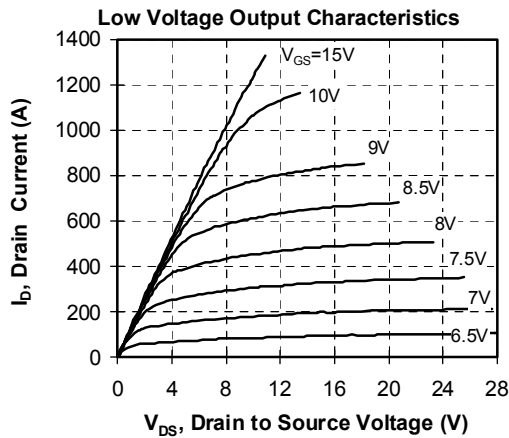
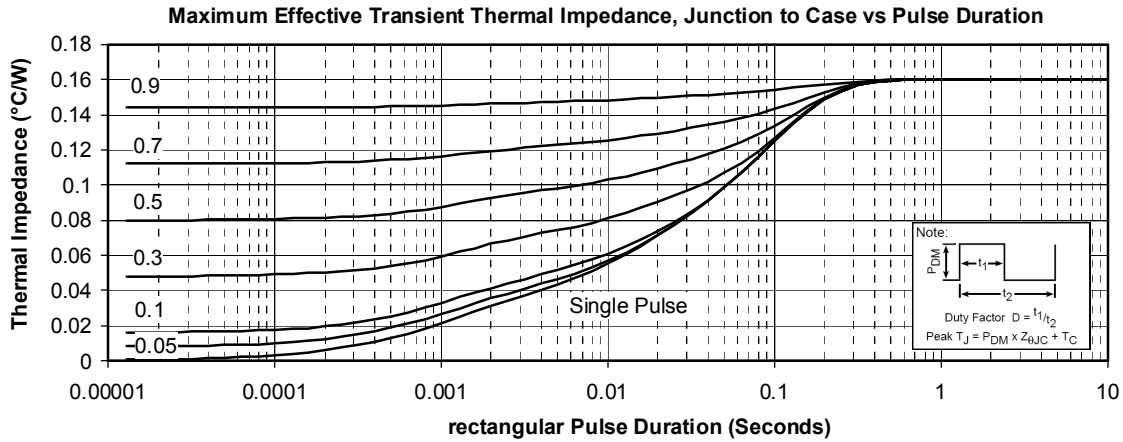
R _{thJC}	Junction to Case Thermal Resistance	Transistor			0.16	°C/W
		Diode			0.29	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz		2500			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				280	g

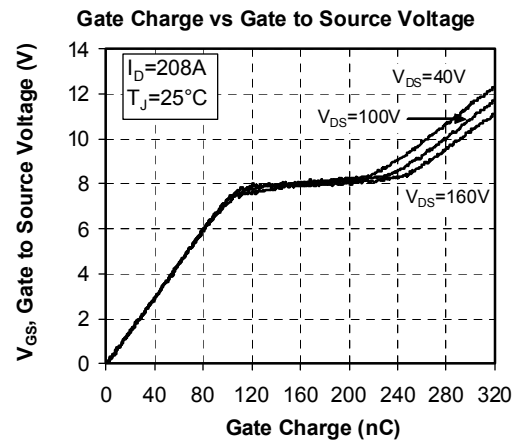
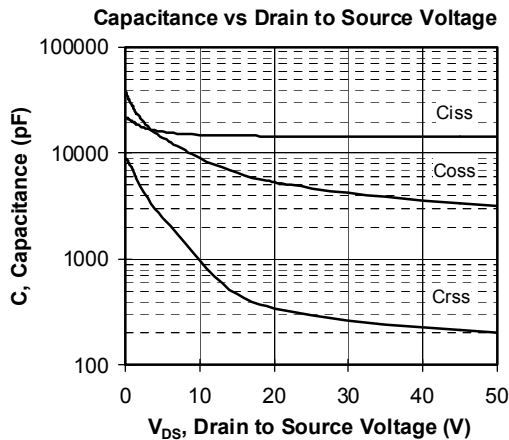
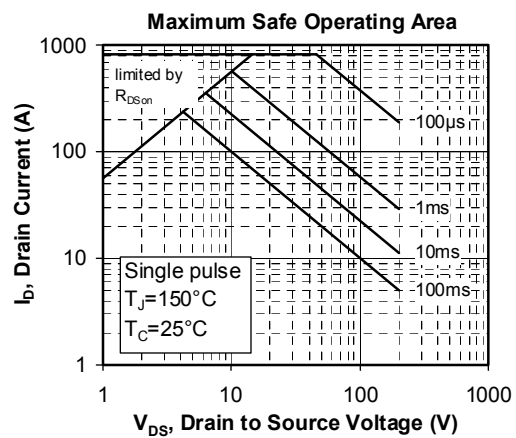
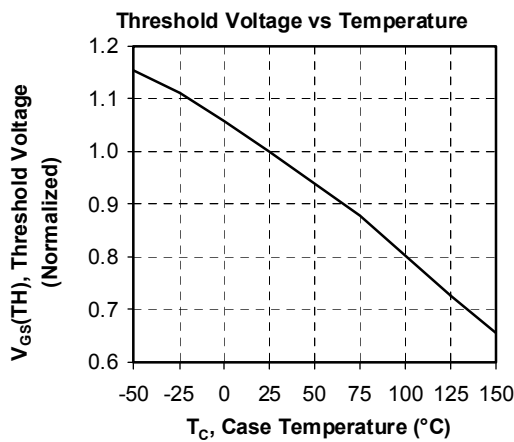
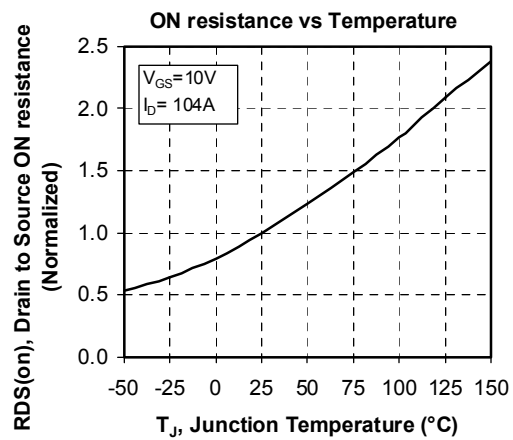
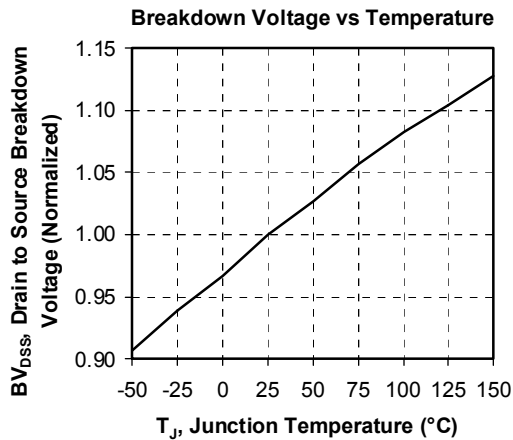
SP6 Package outline (dimensions in mm)



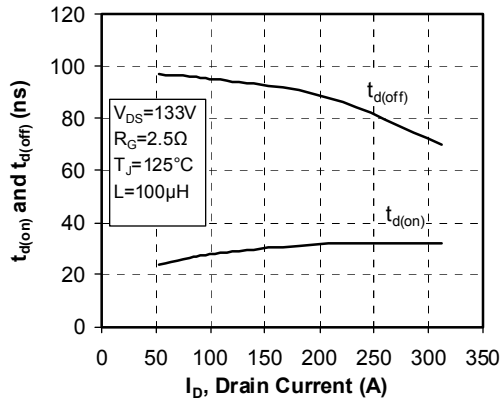
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve

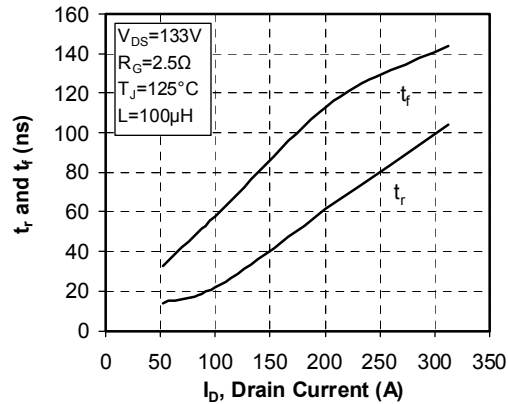




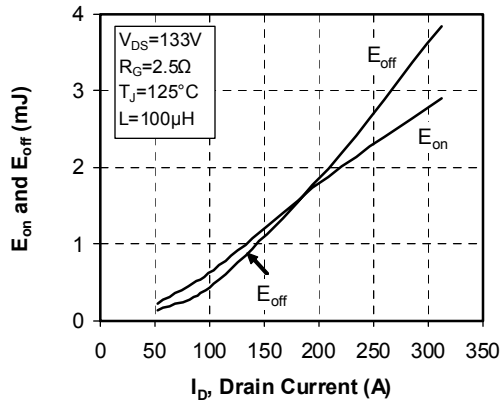
Delay Times vs Current



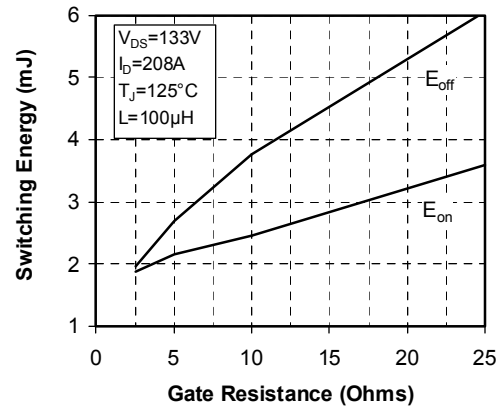
Rise and Fall times vs Current



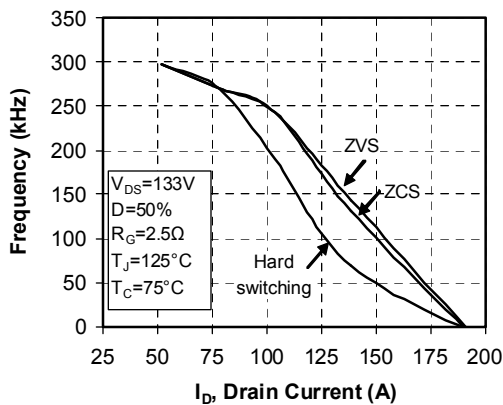
Switching Energy vs Current



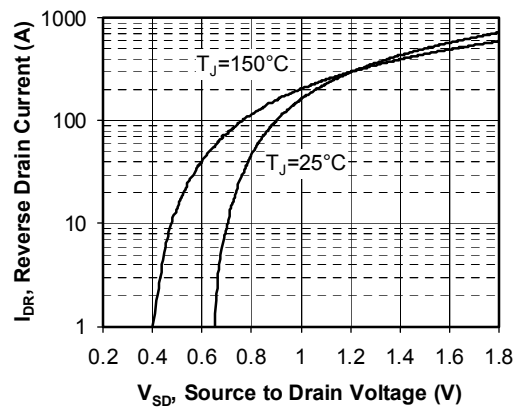
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.